

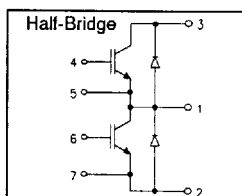
International Rectifier

IRGT10075M12

"HALF-BRIDGE" INT-A-PAK™ MODULES

Fast™ IGBT

- Rugged Design
- Simple gate-drive
- Fast operation up to 10 kHz hard switching, or 50 kHz resonant
- Switching-Loss Rating includes all "tail" losses
- Short circuit rated



$$V_{CE} = 1200V$$

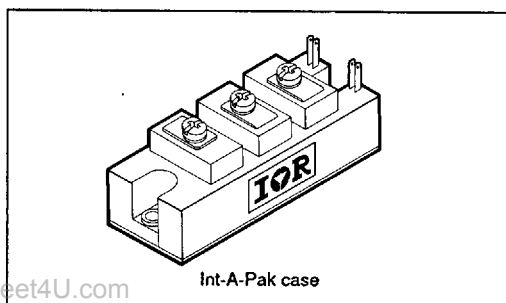
$$I_{C(DC)} = 75A$$

$$V_{CE(SAT)} < 2.8V$$

$$t_{sc} > 10\mu sec$$

Description

IR's advanced IGBT technology is the key to this line of INT-A-pak Power Modules. The efficient geometry and unique processing of the IGBT allow higher current densities than comparable bipolar power module transistors, while at the same time requiring the simpler gate-drive of the familiar power MOSFET. These modules are short circuit rated for applications such as motor control requiring this important feature.



Absolute Maximum Ratings

Parameter	Description	Value	Units
$I_C @ T_C = 25^\circ C$	Continuous collector current	75	A
$I_C @ T_C = 100^\circ C$	Continuous collector current	45	
I_{LM}	Peak switching current	150	
I_{FM}	Peak diode forward current (1)	150	
V_{CE}	Continuous collector to emitter voltage	1200	V
V_{GE}	Gate to emitter voltage	± 20	
V_{ISOL}	RMS isolation voltage, any terminal to case, $t = 1$ min	2500	
$P_D @ T_C = 25^\circ C$	Power dissipation	380	W
T_J	Operating junction temperature range	-40 to 150	°C
T_{STG}	Storage temperature range	-40 to 125	

(1) Duration limited by max junction temperature.

IRGTI0075M12

Electrical Characteristics - $T_J = 25^\circ\text{C}$, unless otherwise stated

Parameter	Description	Min	Typ	Max	Units	Test Conditions
$V_{(BR)CES}$	Collector-to-emitter breakdown voltage	1200	---	---	V	$V_{GE} = 0V, I_C = 1.5mA$
$V_{CE(ON)}$	Collector-to-emitter voltage $T_J = 150^\circ\text{C}$	---	2.4	2.8		$V_{GE} = 15V, I_C = 75A$
		---	1.9	---		$V_{GE} = 15V, I_C = 38A$
		---	---	3.2		$I_F = 75A$
V_{FM}	Diode forward voltage - maximum $T_J = 150^\circ\text{C}$	---	2.7	---		$V_{GE} = 0V$
V_{GEth}	Gate threshold voltage	3.0	---	5.5		$I_C = 750\mu A$
ΔV_{GEth}	Threshold voltage temperature coefficient	---	-11	---	mV/ $^\circ\text{C}$	$V_{CE} = V_{GE}, I_C = 750\mu A$
g_{fe}	Forward transconductance	27	---	53	s	$V_{CE} = 25V, I_C = 75A$
I_{CES}	Collector-to-emitter leakage current $T_J = 150^\circ\text{C}$	---	---	1.5	mA	$V_{GE} = 0V, V_{CE} = 1200V$
		---	---	15		
I_{GES}	Gate-to-emitter leakage current	---	---	± 1.5	μA	$V_{GE} = \pm 20V$

Dynamic Characteristics - $T_J = 125^\circ\text{C}$

Parameter	Description	Min	Typ	Max	Units	Test Conditions
E_{on}	Turn-on switching energy	---	0.19	---	mJ/A	$R_G = 10\Omega, V_{CC} = 600V$
E_{off}	Turn-off switching energy	---	0.36	---		$I_C = 75A$
$E_{ts(1)}$	Total switching energy	---	---	0.6		$V_{GE} = \pm 15V$
$t_{d(on)}$	Turn-on delay time	---	150	250	ns	$R_G = 10\Omega, V_{CC} = 600V$
t_r	Rise time	---	300	450		$I_C = 75A$
$t_{d(off)}$	Turn-off delay time	---	200	300		$V_{GE} = \pm 15V$
t_f	Fall time	---	650	---		$L_S = 100nH$
I_{rr}	Diode peak recovery current	---	36	---	A	$R_G = 10\Omega, V_{CC} = 600V$
t_{rr}	Diode peak recovery time	---	220	---	ns	$I_C = 75A$
Q_{rr}	Diode peak recovery charge	---	4.5	---	μC	$V_{GE} = \pm 15V$
Q_{ge}	Gate-to-emitter charge (turn-on)	35	---	130	nC	$V_{CC} = 600V$
Q_{gc}	Gate-to-collector charge (turn-on)	120	---	250		$I_C = 75A$
Q_g	Total gate charge (turn-on)	380	---	680		$V_{GE} = 15V$
C_{ies}	Input capacitance	8000	---	8300	pF	$V_{GE} = 0V$
C_{oes}	Output capacitance	490	---	820		$V_{CC} = 30V$
C_{res}	Reverse transfer capacitance	490	---	750		$f = 1MHz$
t_{sc}	Short circuit withstand time	10	---	---	μs	$V_{CC} = 750V, V_{GE} = \pm 15V$ min. $R_G = 10\Omega, V_{CEP} = 1000V$

(1) Includes "Tail" losses

Thermal and Mechanical Characteristics

Parameter	Description	Typ	Max	Units
R_{thJC} (IGBT)	Thermal resistance, junction to case, each IGBT	---	0.33	$^\circ\text{C/W}$
R_{thJC} (Diode)	Thermal resistance, junction to case, each diode	---	0.35	
R_{thCS} (Module)	Thermal resistance, case to sink	0.1	---	
Wt	Weight of module	150	---	g

Ordering Information Table

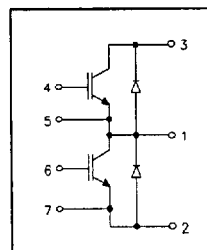
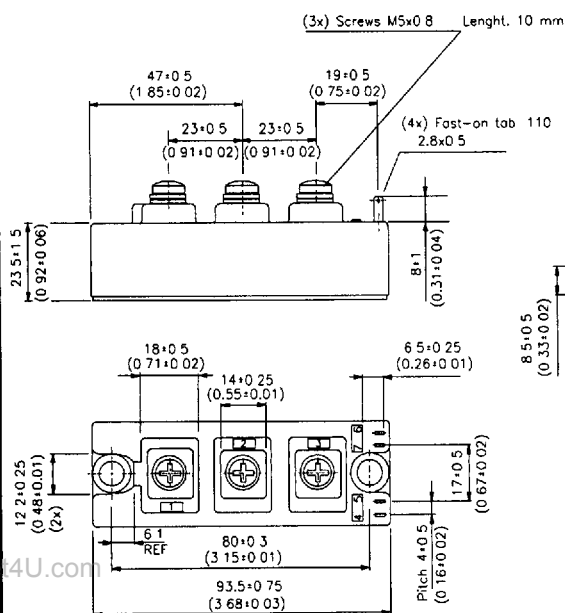
Device Code

IR	G	T	I	0075	M	12
1	2	3	4	5	6	7

- 1** - IR Logo
- 2** - IGBT
- 3** - Function: T = Half-Bridge
- 4** - Package: I = Int-A-Pak
- 5** - Current rating: 0075 = 75A
- 6** - Speed: M = Fast, short circuit rated
- 7** - Voltage rating: 12 = 1200V

Outline Table

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Mechanical Specifications

- Mounting torque
 - Case to heatsink: 5Nm
 - Case to terminal 1-2 & 3: 4Nm, for screws M5x0.8

All dimensions in millimeters (inches)

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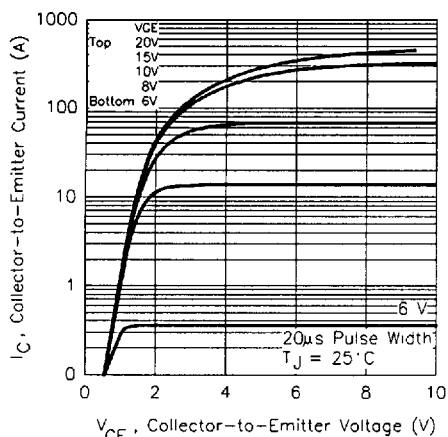
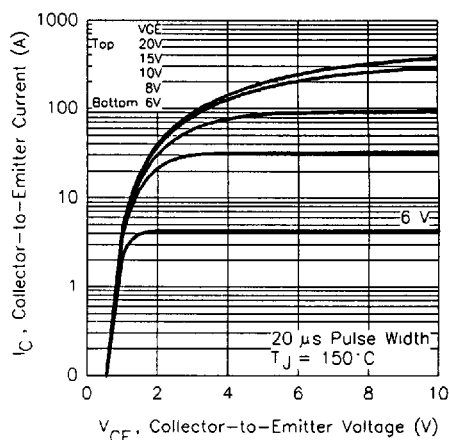
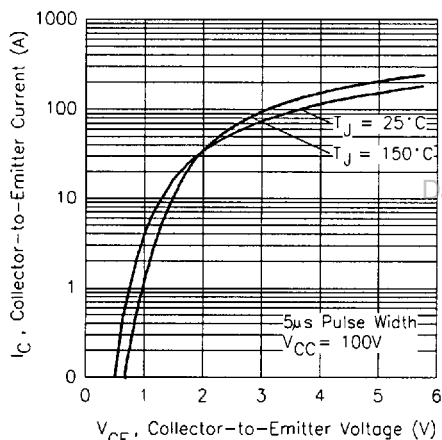
Fig. 1 - Typical Output Characteristics, $T_J = 25^\circ\text{C}$ Fig. 2 - Typical Output Characteristics, $T_J = 150^\circ\text{C}$ 

Fig. 3 - Typical Output Characteristics

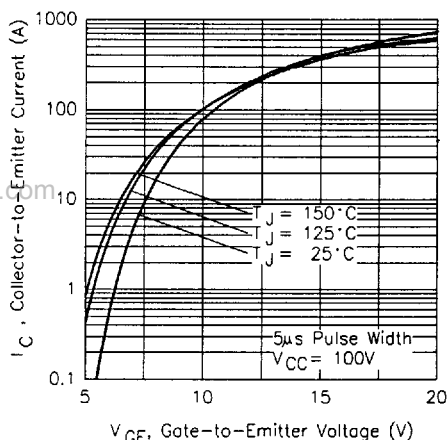


Fig. 4 - Typical Transfer Characteristics

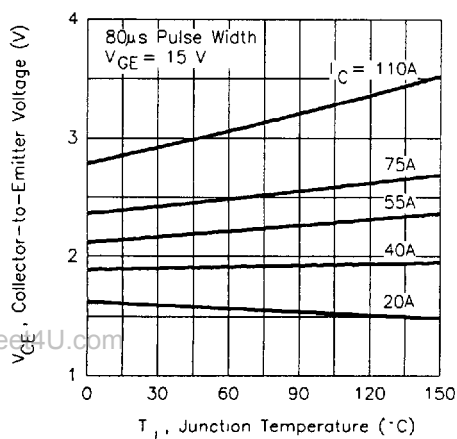
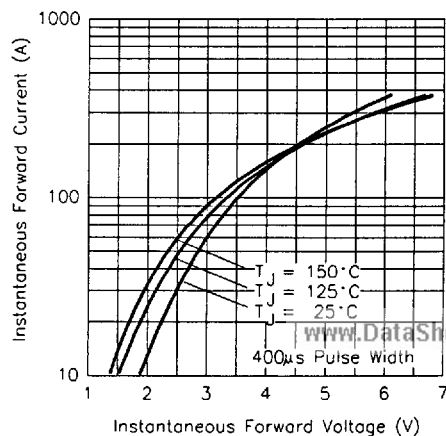
Fig. 5 - Collector-to-Emitter Saturation
Typical Voltage vs. Junction Temperature

Fig. 6 - Forward Voltage Drop Characteristics

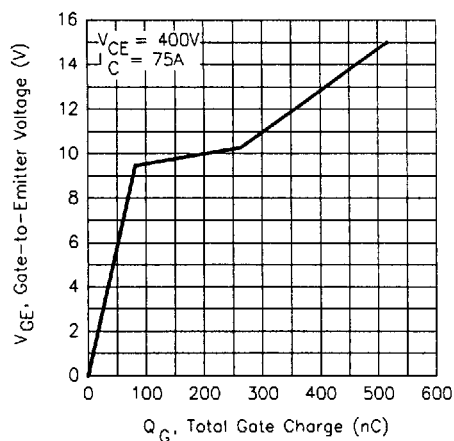


Fig. 7 - Typical Gate Charge vs. Gate-to-Emitter Voltage

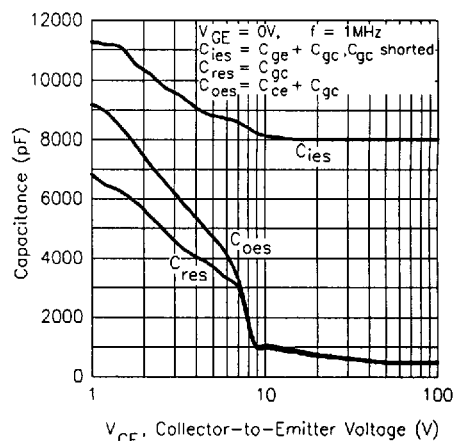


Fig. 8 - Typical Capacitance vs. Collector-to-Emitter Voltage

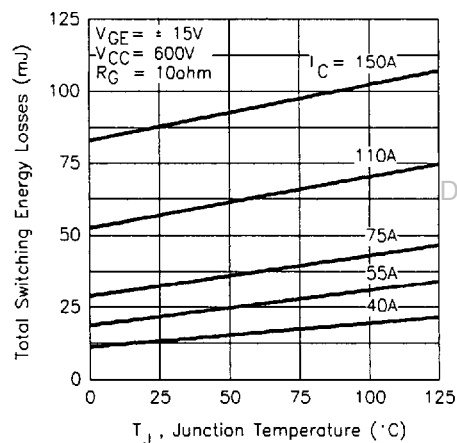


Fig. 9 - Typical Switching Losses vs. Junction Temperature

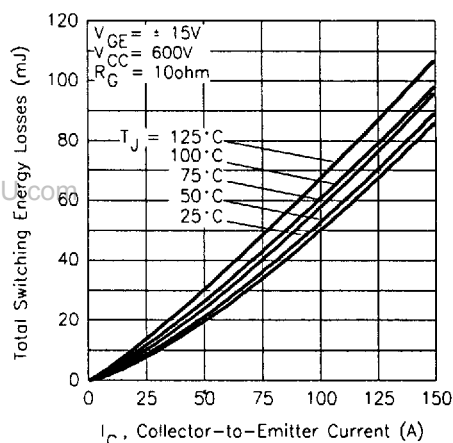


Fig. 10 - Typical Switching Losses vs. Collector-to-Emitter Current

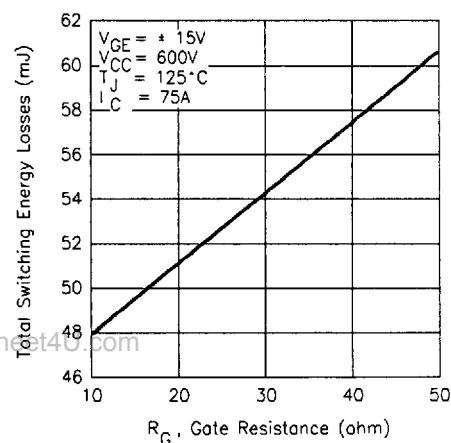


Fig. 11 - Typical Switching Losses vs. Gate Resistance

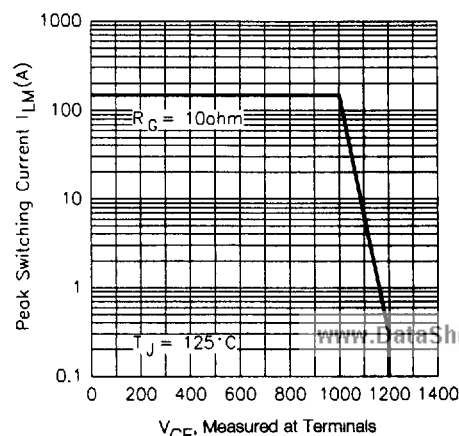


Fig. 12 - Safe Operating Area for Repetitive Switching

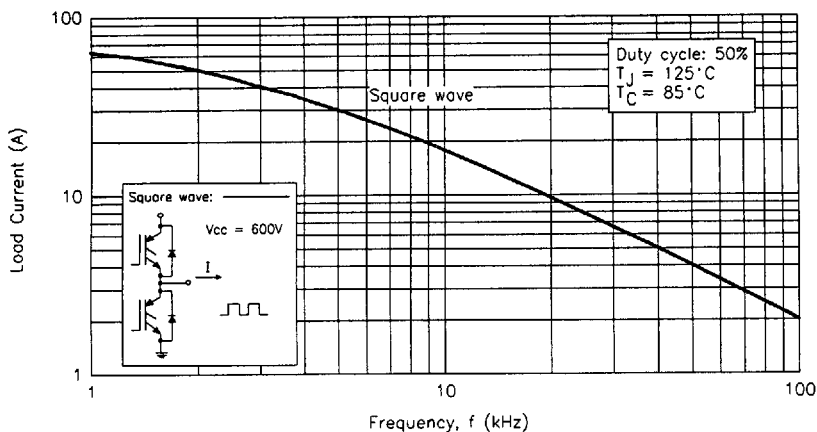


Fig. 13 - Typical Load Current vs. Frequency
(For square wave, $I = I_{RMS}$ of fundamental; for triangular wave, $I = I_{pk}$)

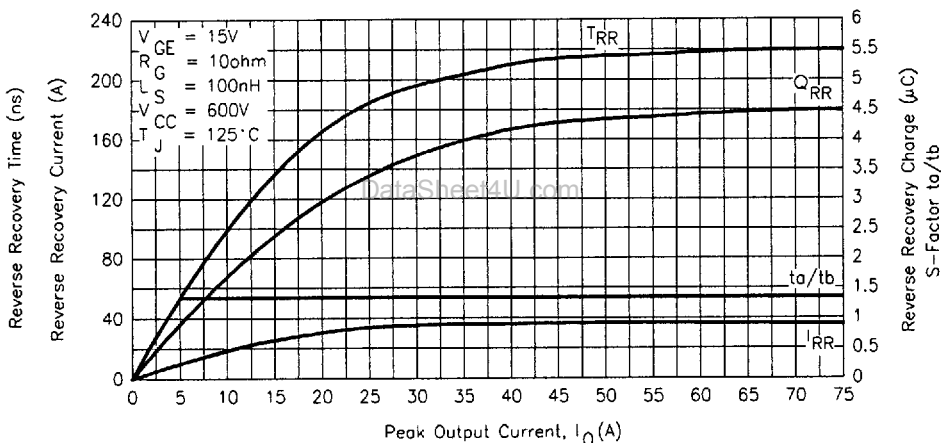


Fig. 14 - Typical Diode Recovery Characteristics as Function of Output Current I_O

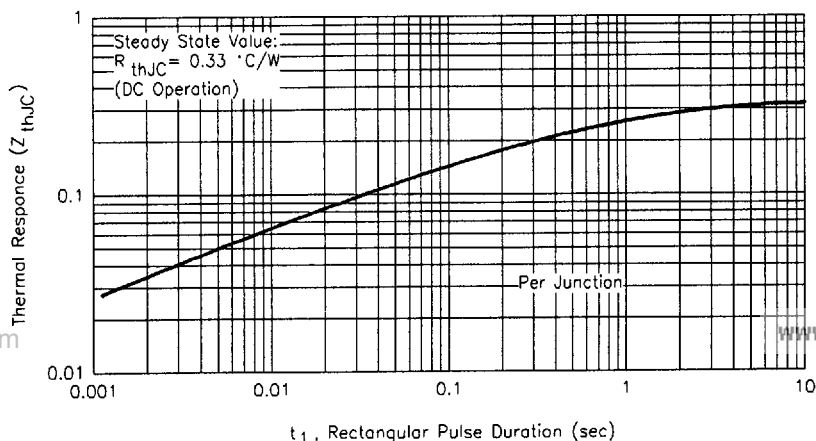
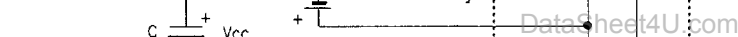


Fig. 15 - Maximum Effective Transient Thermal Impedance, Junction-to-Case



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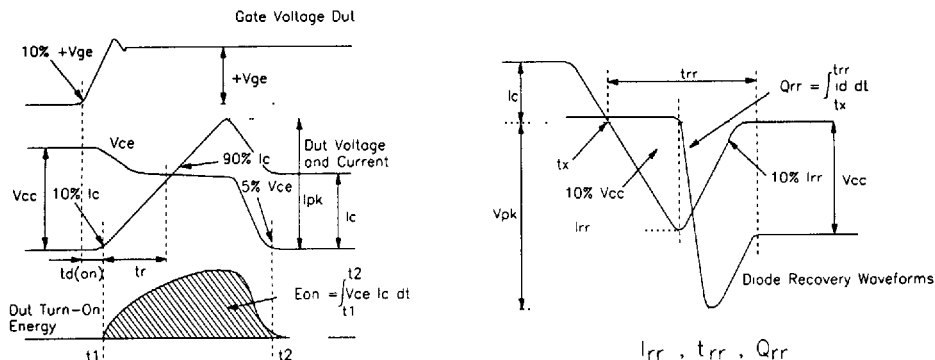


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Fig. 19 - Test Waveforms for Circuit of Fig. 17, Defining E_{ON} , E_{REC} , Q_{RR}

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